MOSFET – Power, Dual N-Channel Logic Level, Dual SO-8FL

60 V, 58 A, 13 mΩ

NVMFD5873NL

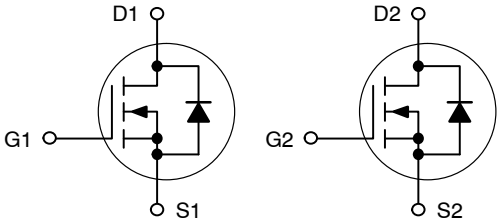
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
60 V	13 mΩ @ 10 V	58 A
	16.5 mΩ @ 4.5 V	

DFN8 5x6
(SO8FL)
CASE 506BT

Features

- Small Footprint (5x6 mm) for Compact Designs
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- NVMFD5873NLWF – Wettable Flanks Option for Enhanced Optical Inspection
- AEC–Q101 Qualified and PPAP Capable
- This is a Pb–Free Device

Dual N–Channel



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Symbol	Parameter			Value	Unit
V_{DSS}	Drain–to–Source Voltage			60	V
V_{GS}	Gate–to–Source Voltage			±20	V
I_D	Continuous Drain Current $R_{\Psi J-mb}$ (Notes 1, 2, 3, 4)	Steady State	T_{mb} = 25°C	58	A
			T_{mb} = 100°C	41	
P_D	Power Dissipation $R_{\Psi J-mb}$ (Notes 1, 2, 3)		T_{mb} = 25°C	107	W
			T_{mb} = 100°C	54	
I_D	Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3 & 4)	Steady State	T_A = 25°C	10	A
			T_A = 100°C	7.0	
P_D	Power Dissipation $R_{\theta JA}$ (Notes 1 & 3)		T_A = 25°C	3.1	W
			T_A = 100°C	1.6	
I_{DM}	Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		190	A
T_J, T_{stg}	Operating Junction and Storage Temperature			−55 to 175	°C
I_S	Source Current (Body Diode)			58	A
E_{AS}	Single Pulse Drain–to–Source Avalanche Energy (T_J = 25°C, V_{GS} = 10 V, $I_{L(pk)}$ = 28.3 A, L = 0.1 mH, R_G = 25 Ω)			40	mJ
T_L	Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			260	°C

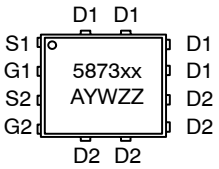
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
$R_{\Psi J-mb}$	Junction–to–Mounting Board (top) – Steady State (Notes 2, 3)	1.4	°C/W
$R_{\theta JA}$	Junction–to–Ambient – Steady State (Note 3)	48	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51–12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface–mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
4. Maximum current for pulses as long as 1 second are higher but are dependent on pulse duration and duty cycle.

MARKING DIAGRAM



5873NL = Specific Device Code for NVMFD5873NL
5873LW = Specific Device Code for NVMFD5873NLWF
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 5.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
$V_{(BR)DSS}$	Drain−to−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA		60			V
$V_{(BR)DSS}/T_J$	Drain−to−Source Breakdown Voltage Temperature Coefficient				54.9		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0 V, V_{DS} = 60 V	T_J = 25°C			1.0	μA
			T_J = 125°C			100	
I_{GSS}	Gate−to−Source Leakage Current	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 7)							
$V_{GS(TH)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA		1.5		2.5	V
$V_{GS(TH)}/T_J$	Threshold Temperature Coefficient				−5.8		mV/°C
$R_{DS(on)}$	Drain−to−Source On Resistance	V_{GS} = 10 V, I_D = 15 A			10.7	13	mΩ
		V_{GS} = 4.5 V, I_D = 10 A			13.6	16.5	
g_{FS}	Forward Transconductance	V_{DS} = 5.0 V, I_D = 15 A			15		S
CHARGES AND CAPACITANCES							
C_{iss}	Input Capacitance	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 25 V			1560		pF
C_{oss}	Output Capacitance				145		
C_{rss}	Reverse Transfer Capacitance				98		
$Q_{G(TOT)}$	Total Gate Charge	V_{GS} = 4.5 V, V_{DS} = 48 V, I_D = 15 A			16.5		nC
$Q_{G(TH)}$	Threshold Gate Charge				1.3		
Q_{GS}	Gate−to−Source Charge				4.0		
Q_{GD}	Gate−to−Drain Charge				8.8		
$Q_{G(TOT)}$	Total Gate Charge	V_{GS} = 10 V, V_{DS} = 48V, I_D = 15 A			30.5		nC
SWITCHING CHARACTERISTICS (Note 8)							
$t_{d(on)}$	Turn−On Delay Time	V_{GS} = 4.5 V, V_{DS} = 48 V, I_D = 15 A, R_G = 2.5 Ω			10.8		ns
t_r	Rise Time				51		
$t_{d(off)}$	Turn−Off Delay Time				21		
t_f	Fall Time				42.6		
$t_{d(on)}$	Turn−On Delay Time	V_{GS} = 10 V, V_{DS} = 48 V, I_D = 15 A, R_G = 2.5 Ω			9.5		ns
t_r	Rise Time				13		
$t_{d(off)}$	Turn−Off Delay Time				25		
t_f	Fall Time				6.6		
DRAIN−SOURCE DIODE CHARACTERISTICS							
V_{SD}	Forward Diode Voltage	V_{GS} = 0 V, I_S = 15 A	T_J = 25°C		0.8	1.0	V
			T_J = 125°C		0.7		
t_{RR}	Reverse Recovery Time	V_{GS} = 0 V, d_{IS}/d_t = 100 A/μs, I_S = 15 A			22.4		ns
t_a	Charge Time				14.5		
t_b	Discharge Time				9.0		
Q_{RR}	Reverse Recovery Charge				18		nC

5. Pulse Test: pulse width = 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.
7. Pulse Test: pulse width = 300 μs, duty cycle ≤ 2%.
8. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

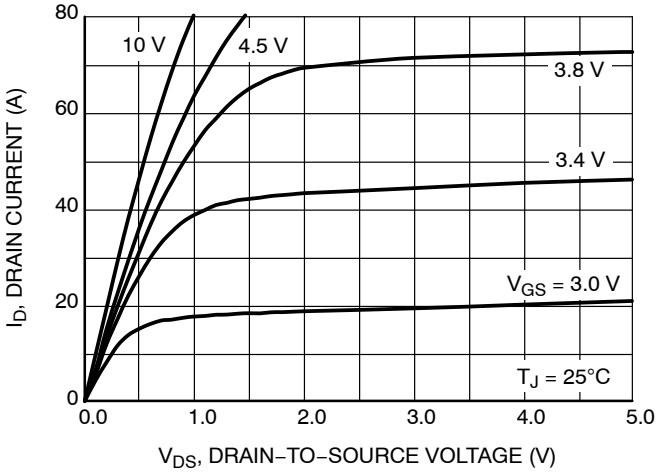


Figure 1. On−Region Characteristics

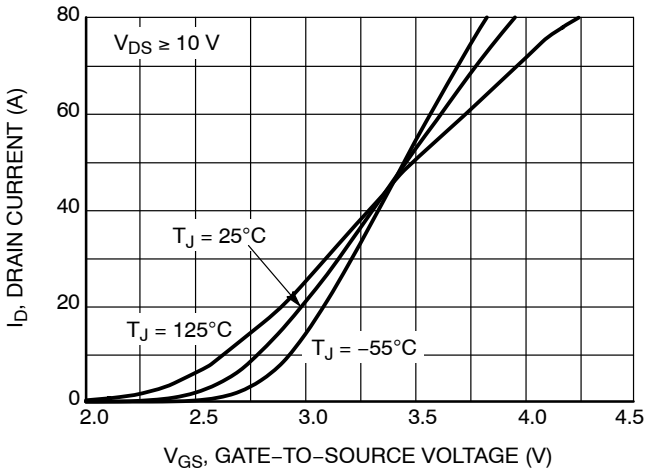


Figure 2. Transfer Characteristics

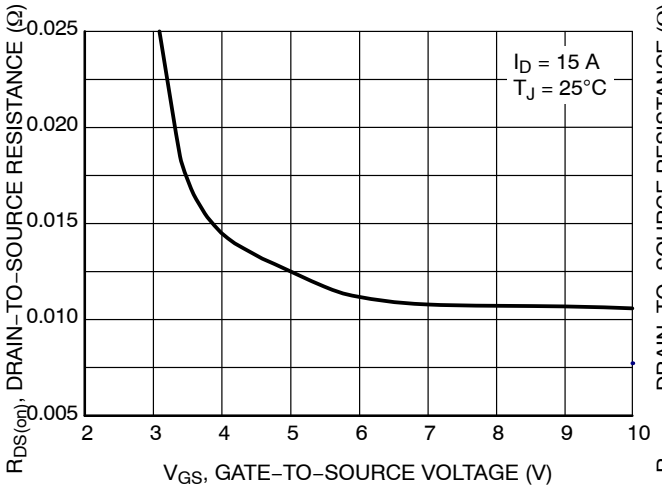


Figure 3. On−Resistance vs. V_{GS}

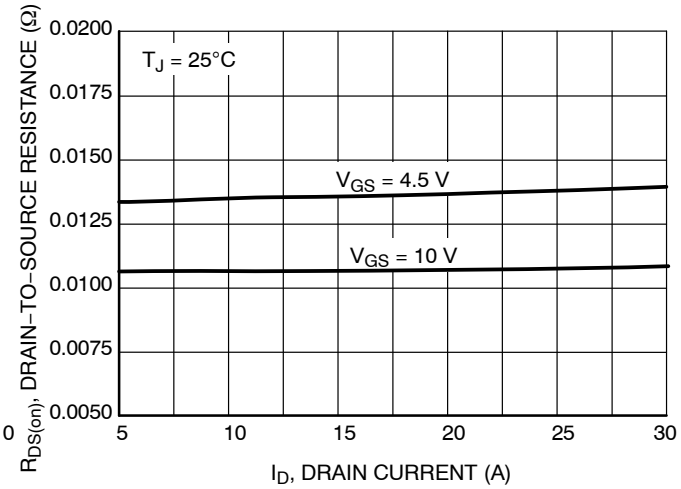


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

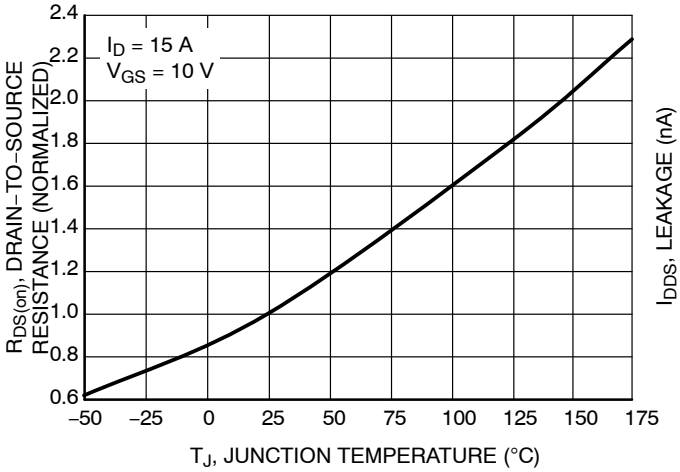


Figure 5. On−Resistance Variation with Temperature

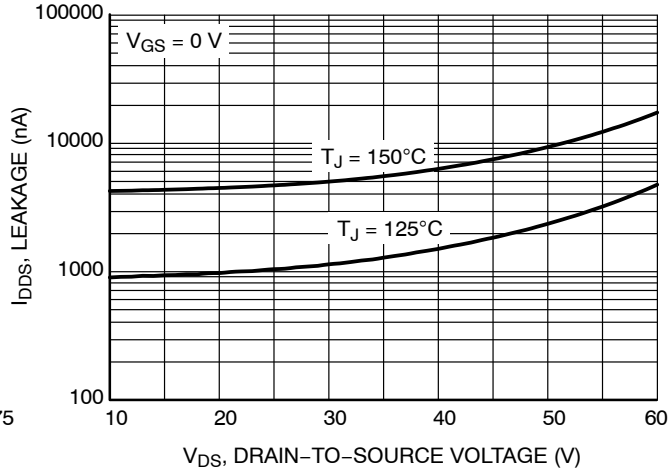


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)

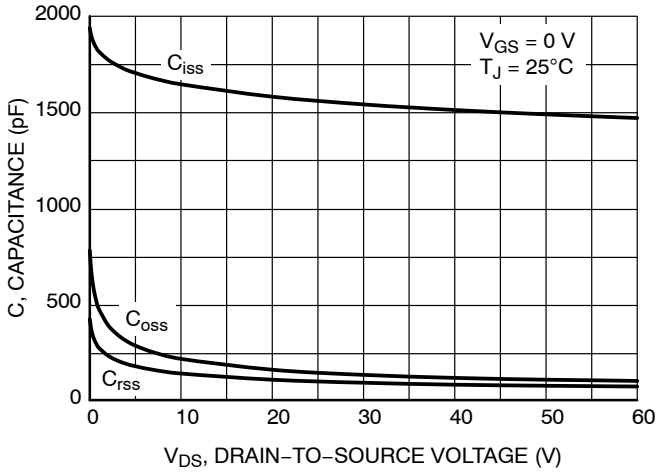


Figure 7. Capacitance Variation

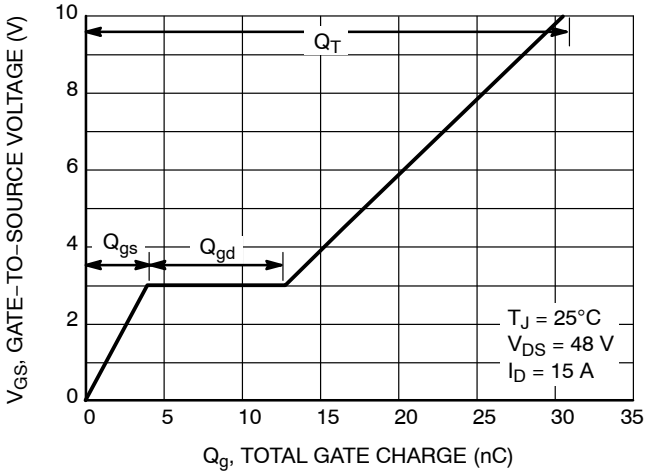


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

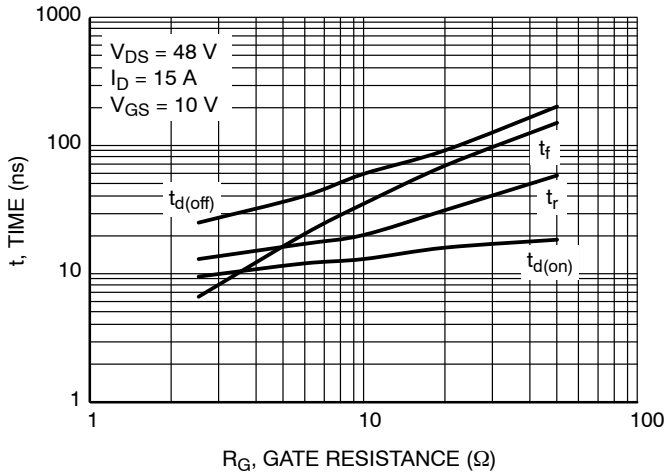


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

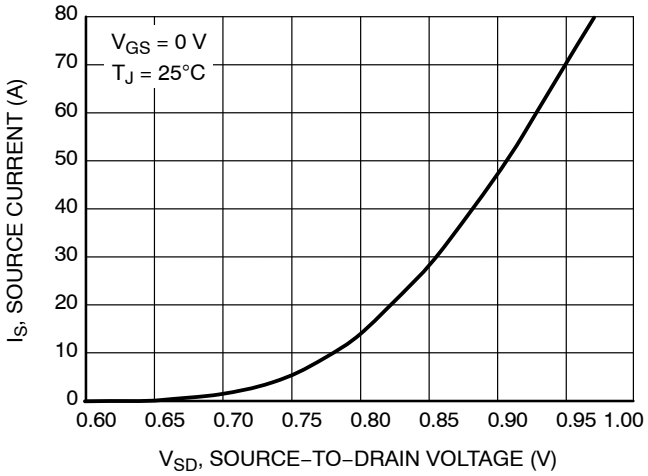


Figure 10. Diode Forward Voltage vs. Current

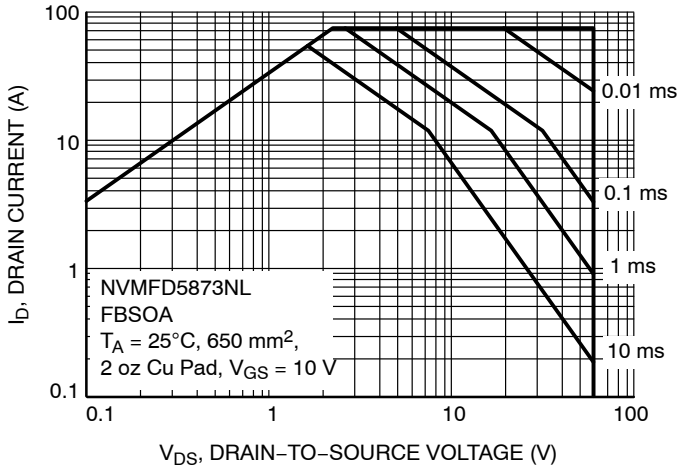


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS (continued)

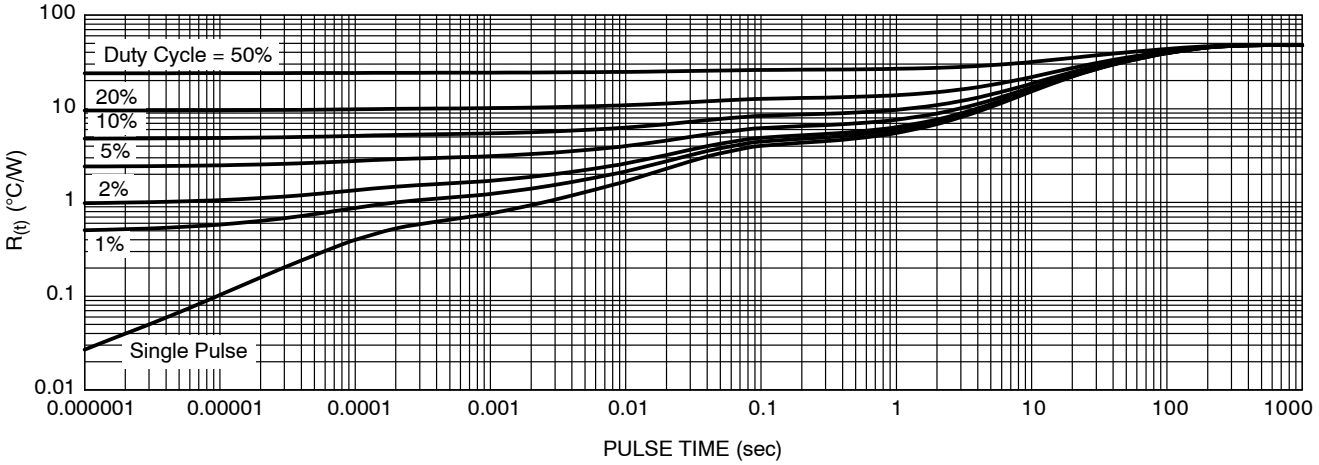


Figure 12. Thermal Response

DEVICE ORDERING INFORMATION

Device	Package	Shippingg†
NVMFD5873NLWFT1G−UM	DFN8 (Pb−Free)	1,500 / Tape & Reel

DISCONTINUED (Note 9)

NVMFD5873NLT1G	DFN8 (Pb−Free)	1,500 / Tape & Reel
NVMFD5873NLWFT1G	DFN8 (Pb−Free)	1,500 / Tape & Reel

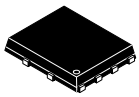
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

9. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

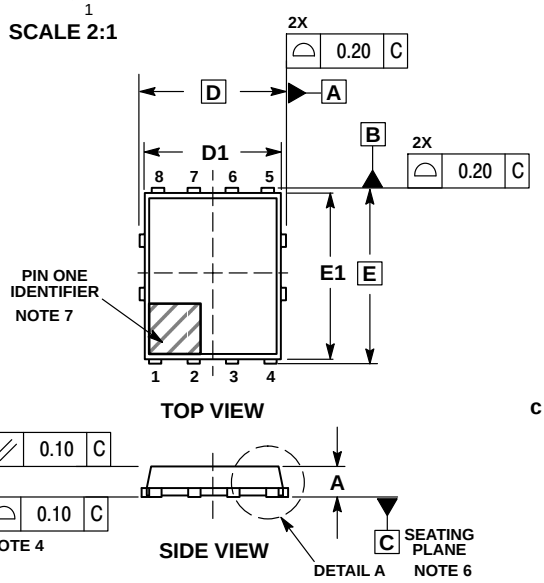
DFN8 5x6, 1.27P Dual Flag (SO8FL−Dual)

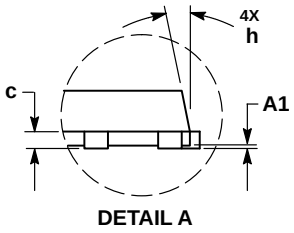
CASE 506BT
ISSUE F

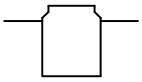
DATE 23 NOV 2021



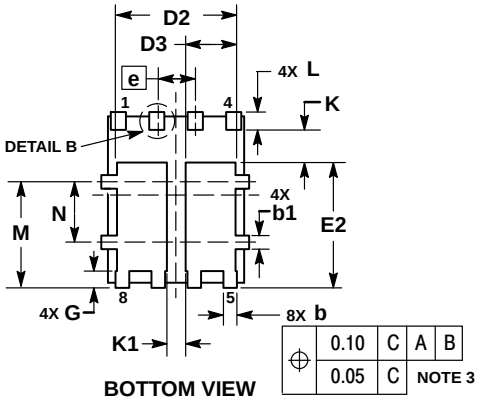
SCALE 2:1







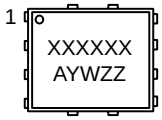
DETAIL B
ALTERNATE CONSTRUCTION



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. PROFILE TOLERANCE APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
7. A VISUAL INDICATOR FOR PIN 1 MUST BE LOCATED IN THIS AREA.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	–––	1.10
A1	–––	–––	0.05
b	0.33	0.42	0.51
b1	0.33	0.42	0.51
c	0.20	–––	0.33
D		5.15 BSC	
D1	4.70	4.90	5.10
D2	3.90	4.10	4.30
D3	1.50	1.70	1.90
E		6.15 BSC	
E1	5.70	5.90	6.10
E2	3.90	4.15	4.40
e		1.27 BSC	
G	0.45	0.55	0.65
h	–––	–––	12 °
K	0.51	–––	–––
K1	0.56	–––	–––
L	0.48	0.61	0.71
M	3.25	3.50	3.75
N	1.80	2.00	2.20

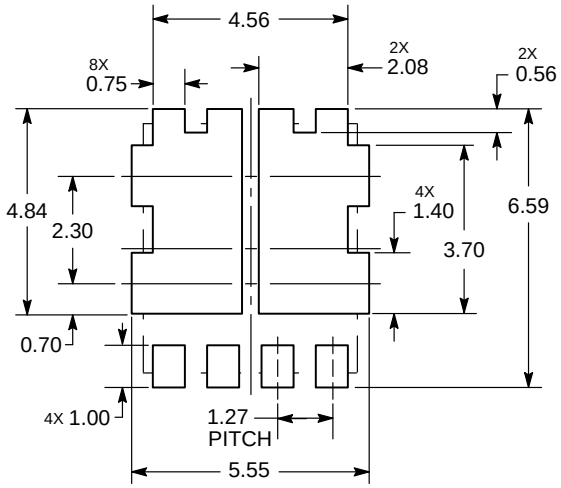
GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON50417E**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**DFN8 5X6, 1.27P DUAL FLAG (SO8FL−DUAL)**		**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales